

ABSTRACT OF THE DISCLOSURE

A semiconductor device has a configuration in which more than three kinds of wells are formed with small level differences. One kind of well from among  
5 the more than three kinds of wells has a surface level higher than other kinds of wells from among the more than three kinds of wells. The one kind of well is formed adjacent to and self-aligned to at least one kind of well from among the other kinds of wells. The other  
10 kinds of wells are different in one of a conductivity type, an impurity concentration and a junction depth, and include at least two kinds of wells having the same surface level.